

## M agnetic F ield I nduced S pin P olarization of A l A s T wo-dim ensional E lectrons

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Two-dimensional (2D) electrons in an in-plane magnetic field become fully spin polarized above a field  $B_F$ , which we can determine from the in-plane magnetoresistance. We perform such measurements in modulation-doped AlAs electron systems, and find that the field  $B_F$  increases approximately linearly with 2D electron density. These results imply that the product  $\tilde{g}m^*$ , where  $\tilde{g}$  is the effective  $g$ -factor and  $m^*$  the effective mass, is a constant essentially independent of density. While the deduced  $\tilde{g}m^*$  is enhanced relative to its band value by a factor of 4, we see no indication of its divergence as 2D density approaches zero. These observations are at odds with results obtained in Si-MOSFETs, but qualitatively confirm spin polarization studies of 2D GaAs carriers.

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The ground state properties of dilute 2D carrier systems are still under close scrutiny, and several issues, such as the existence of a metal-insulator transition and the occurrence of a ferromagnetic instability at zero magnetic fields, remain largely unresolved. At the lowest densities ( $n$ ), calculations predict that 2D electrons settle into a Wigner crystal [1], while at the highest  $n$ , a paramagnetic Fermi liquid model most likely describes the ground state of the 2D electron system (2DES). At intermediate densities, a Stoner transition to a fully spin polarized ground state may take place [1, 2, 3, 4, 5], but experimental evidence for such a phase has been scant so far. A semi-direct method used to probe this ferromagnetic state involves measuring the product  $\tilde{g}m^*$  in the 2D electron system at various densities. A diverging  $\tilde{g}m^*$  as  $n$  approaches a critical density, would then imply that the system spontaneously polarizes at lower  $n$ . Accordingly, several groups have recently studied the density dependence of  $\tilde{g}m^*$  in dilute 2D carrier systems, but have not yet reached an agreement. Some of these groups have reported an increasing  $\tilde{g}m^*$  as  $n$  decreases in Si-MOSFETs [6, 7, 8, 9, 10]. Furthermore, scaling arguments based on in-plane magnetoresistance of electrons in the same system [9, 10] suggest that  $\tilde{g}m^*$  diverges at a finite density, hinting at a possible Stoner instability. On the other hand, measurements of  $\tilde{g}m^*$  in 2D carrier systems in GaAs [11, 12, 13] point to the contrary. Direct measurements of the magnetization of Si 2D electrons also offer no evidence for a ferromagnetic ground state [14].

In an attempt to resolve these discrepancies, we have performed experiments in a new system, 2D electrons in AlAs, in which the effect of disorder is very much reduced: we have recently obtained AlAs samples with electron mobilities as high as  $30 \text{ m}^2/\text{Vs}$  [15]. For similar  $r_s$ , defined as the ratio of average interparticle separation to the effective Bohr radius, mobilities in AlAs are roughly an order of magnitude larger than those in Si, and a factor 2 lower than in GaAs. We find that  $\tilde{g}m^*$  in AlAs 2D electrons is approximately independent of density for

the measured range  $0.5 < n < 5.9 \times 10^{11} \text{ cm}^{-2}$ . Our results imply that the ground state of the AlAs 2DES remains unpolarized at all measured densities, a conclusion in agreement with transport experiments in GaAs and with magnetization measurements in Si [14].

The electronic band structure of AlAs is reminiscent of that of Si: conduction electrons in AlAs, located at the  $X$ -point of the Brillouin zone, have an isotropic effective mass ( $m_l = 1.0$ ,  $m_t = 0.2$ ) almost identical to that of Si, and a band  $g$ -factor equal to 2, as in Si [16]. In 2D however, properties of Si and AlAs electrons are different: AlAs (100) 2D electrons in quantum wells wider than 45 Å [17, 18] occupy  $X$ -point valleys with principal axes parallel to the plane of the 2DES, so that their cyclotron effective mass is  $m_b = (m_l m_t)^{1/2} = 0.46$  [19], while in Si (100), out-of-plane valleys are occupied, and  $m_b = m_t = 0.2$  (effective masses are given in units of the free electron mass). Strain induced by lattice mismatch between the AlAs quantum well and AlGaAs barriers is responsible for increasing the energy of the out-of-plane valleys in AlAs relative to the energy of the in-plane valleys, so that for wide AlAs quantum wells, such as those used in our study, in-plane valleys are occupied. In Si-MOSFETs and in narrow AlAs quantum wells, on the other hand, out-of-plane plane valleys are populated due to the higher effective mass in the growth direction.

Results for three samples (A-C) are presented here. These were grown by molecular beam epitaxy atop a GaAs (411)B substrate for sample A (M393IV-D2), and GaAs (100) substrates for samples B (M420-D3) and C (M415-J2). The layer structures for these samples are composed of a 150 Å (samples A and C) or a 120 Å-wide (sample B) AlAs quantum well, sandwiched between  $\text{Al}_{1-x}\text{Ga}_x\text{As}$  barriers, with  $0.25 < x < 0.4$ , and modulation doped with Si. We patterned all samples in a Hall bar geometry for transport measurements in magnetic fields up to 18 T, which were conducted in a  $^3\text{He}$  cryostat with a base temperature of  $T = 300 \text{ mK}$ , and in a dilution refrigerator for  $T$  down to 30 mK. Samples were mounted on a single-axis rotator stage, which al-

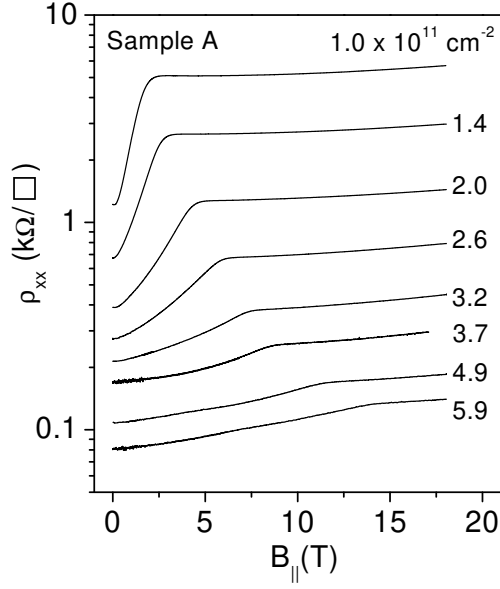


FIG. 1: In-plane magnetoresistance of GaAs 2D electrons for different carrier densities in sample A at  $T = 30$  mK. Magnetoresistance increases strongly at low fields, and saturates or increases more slowly at higher fields, when the 2DES is fully polarized.

allowed us to tune the angle between the magnetic field direction and the plane of the 2D electron system. After illumination, carrier density was varied with the help of both front- and back-gates, and was determined from Shubnikov-de Haas oscillations measured in a perpendicular magnetic field. In sample A, electron mobility at  $T = 30$  mK ranged from  $\mu = 5.6$  m<sup>2</sup>/Vs at  $n = 1.2 \times 10^{11}$  cm<sup>-2</sup> to  $\mu = 14$  m<sup>2</sup>/Vs at  $n = 5.9 \times 10^{11}$  cm<sup>-2</sup>.

In-plane magnetoresistance data ( $\rho_{xx}$ ) for sample A are plotted in Fig. 1 for several carrier densities. As in Si MOSFETs, the resistivity shows a strong increase with  $B_{||}$  at low fields, while it rises much more slowly beyond a crossover field  $B_P$ . Based on experimental [7, 11, 12, 20] and theoretical [21] work, it is believed that at  $B_P$  the 2DES undergoes a transition from a partially spin-polarized state to a fully spin-polarized state. For one of the traces shown ( $n = 2.6 \times 10^{11}$  cm<sup>-2</sup>), using a method reported previously [11], we verified that above  $B_P$  the system indeed becomes spin-polarized. We note that Pudalov et al. [22] have reported that the crossover field in Si MOSFETs is sample dependent, and conclude that  $B_P$  does not reflect complete spin polarization of the 2DES. As our results, in contrast, are reproduced in several samples, we follow the assumption that  $B_P$  does reflect full spin polarization of the 2DES. At  $B = B_P$ , the Fermi energy of the system is equal to its Zeeman energy, which gives the following relationship between  $B_P$  and  $\mu$ :

$$B_P = \frac{n}{\mu} \frac{2\hbar}{e}; \quad (1)$$

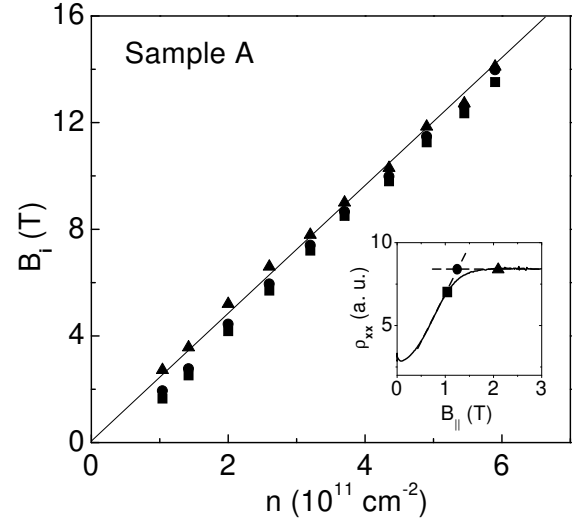


FIG. 2:  $B_{in}$ ,  $B_{id}$ ,  $B_{ax}$  fields vs.  $n$  for sample A ( $T = 30$  mK). Inset: Schematic definition of  $B_{id}$  fields, indicated by squares, circles and triangles respectively. These fields define a range within which spin subband depopulation likely takes place.

valid for a single-valley 2DES [23]. From this equation, and knowing  $B_P$ , we can thus extract the product  $\mu n$ .

The crossover in magnetoresistance in Fig. 1 is not perfectly sharp, but can be described empirically by fitting straight lines to the low- and high- field ranges of the trace (in a linear plot), and defining two respective fields,  $B_{min}$  and  $B_{max}$ , at which  $\rho_{xx}$  deviates from these lines (see Fig. 2 inset). A deviation ratio of 1 % is used for  $B_{min}$ , while we use 0.1 % for  $B_{max}$  [24]. A smaller deviation criterion is used for  $B_{max}$  than for  $B_{min}$ , because  $\rho_{xx}$  departs more abruptly from the straight line fit around  $B_{max}$ . The two deviation points are marked respectively by squares and triangles in the inset of Fig. 2. A third field ( $B_{id}$ ), marked by a circle in Fig. 2, is defined as the intersection between the two lines. For GaAs 2D electrons, full spin polarization likely takes place within the range  $[B_{min}, B_{max}]$ , though we do not know the exact relationship between the actual polarization field  $B_P$  and the range limits. In this paper we assume, as is evidenced in GaAs 2D electrons [11] and holes [25], that  $B_P$  is the upper field  $B_{max}$ . For completeness, we also provide here the range of values,  $[B_{min}, B_{max}]$ , within which  $B_P$  is likely to lie. We note that our conclusion, namely, that  $\mu n$  does not increase as  $n$  decreases, does not depend on the choice of  $B_P$  within the range  $[B_{min}, B_{max}]$ .

We plot in Fig. 2 the three  $B_{i}$  fields  $B_{min}$ ,  $B_{id}$ , and  $B_{max}$ , obtained from the traces in Fig. 1, as a function of sample density. These values increase remarkably linearly with density, and a fit through the upper fields  $B_{max}$  appears to intercept the horizontal axis at a density small enough as to be identified with zero, within

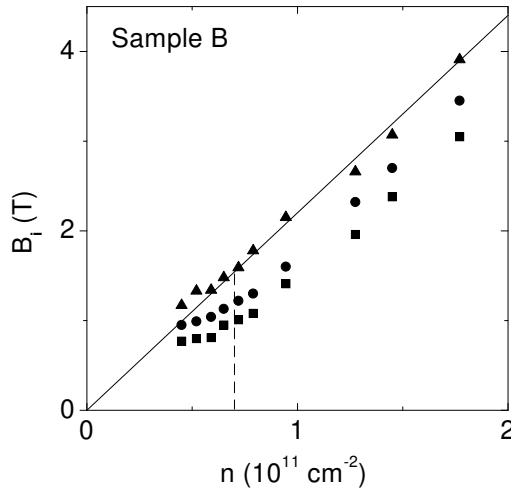


FIG. 3:  $B_i$  fields vs.  $n$  for sample B ( $T = 300$  mK). The fields decrease linearly with decreasing  $n$  over most of the range, but tend to saturate at low  $n$ . The dashed line indicates the density at the apparent zero-field metal-insulator transition.

error margins. In Fig. 3, similar data is plotted for sample B at  $T = 300$  mK, for a lower density range. For  $n < 1 \times 10^{11} \text{ cm}^{-2}$ , the data points do not decrease linearly as  $n$  is lowered, but appear to extrapolate to a finite field at zero density. To verify that this saturation does not result from the finite temperature of measurements, we record the  $B_i$  fields for several temperatures [Fig. 4 (a-c)]. For all measured densities, the fields  $B_{min}$  and  $B_{mid}$  are approximately independent of  $T$  for  $T < 300$  mK [26]. In Fig. 4 (d) we also plot the temperature dependence of  $R_{xx}$  ( $B_{jj}$ ) for the lower two densities in sample A. As for GaAs electrons and holes [1, 12, 13, 25] and for Si electrons [7, 27], we observe a transition from metallic to insulating behavior near a finite field  $B_c$ , lower than  $B_{min}$ . We also note that the apparent zero-field insulating-to-metallic transition in AlAs 2D electrons occurs in sample B at  $n = 0.7 \times 10^{11} \text{ cm}^{-2}$  [28], indicated by a dashed line in Fig. 3, which corresponds approximately to the onset of  $B_i$  saturation as  $n$  is lowered. A similar saturation for  $n < n_c$  seems to also take place in other 2D systems, such as in GaAs holes [13] and in Si MOSFETs [29]. The physics behind this phenomenon may be related to a disorder-induced broadening of the spin subbands, but certainly needs further theoretical and experimental attention.

We conclude this paper by deriving the product  $\tilde{g} \tilde{m}$  from our magnetoresistance data, using Eq. 1. We assume that spin subband depopulation occurs at the field  $B_{max}$  [11, 25], and plot in Fig. 5 the deduced  $\tilde{g} \tilde{m}$  for several AlAs samples (including samples A and B [30]), normalized to their band values using  $g_b = 2.0$ , and  $m_b = 0.46$  and  $0.41$  for (100) and (411)B-oriented substrates respectively. The magnitude of the  $\tilde{g} \tilde{m}$  enhancement is approximately equal to 4, a value comparable to the

enhanced  $\tilde{g} \tilde{m}$  in GaAs and Si 2D carrier systems for similar  $r_s$ . Remarkably, we also observe that  $\tilde{g} \tilde{m}$  in AlAs is roughly independent of  $n$  for a wide range of densities.

Our results thus contrast with studies of spin polarization in Si MOSFETs, which find that  $\tilde{g} \tilde{m}$  increases at low densities [6, 7, 8, 9, 10]. Authors in Refs. 9 and 10 obtain their conclusions after scaling the magnetoresistance with a single curve independent of  $B$  or  $T$ . We find that for AlAs 2D electrons, no linear mapping of  $B$ ,  $r_{xx}$  or  $r_{xx} (= 1/r_{xx})$  is able to generate such a scaling law. We thus rely solely on Eq. 1 to obtain values for  $\tilde{g} \tilde{m}$ . Our data therefore do not point to a ferromagnetic ground state at any finite density, which is consistent with the behavior of GaAs 2D electrons [11] and holes [12, 13, 25].

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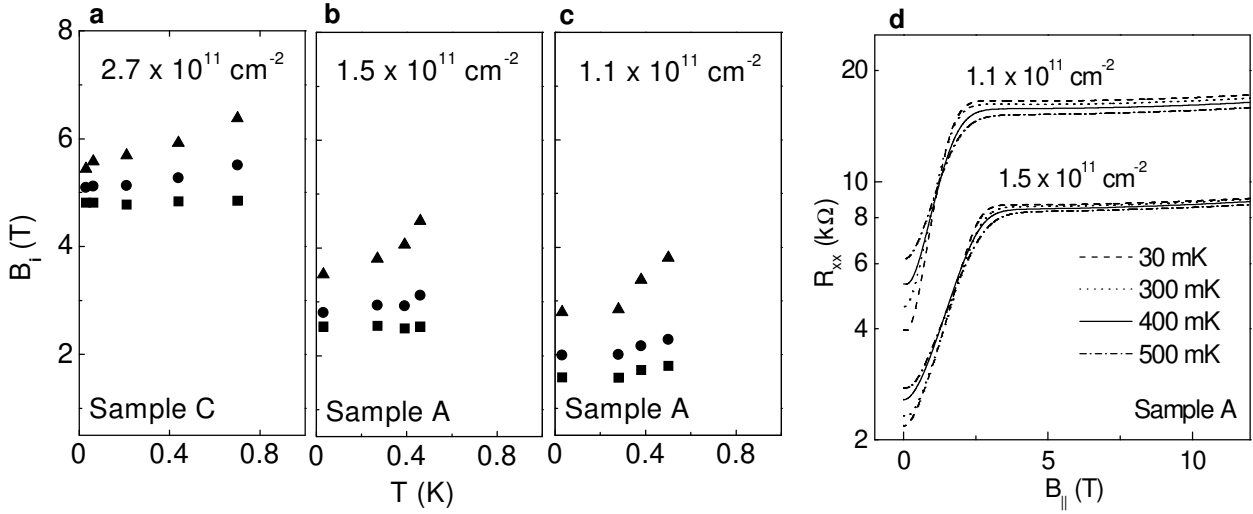


FIG. 4: (a-c) Temperature dependence of  $B_i$  fields (defined in text) for three different densities. Data are shown for sample A in (b) and (c), and for sample C in (a). (d) T dependence of in-plane magnetoresistance of sample A.

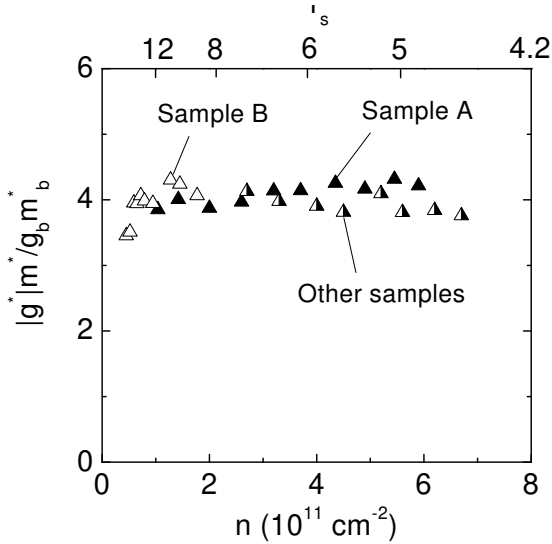


FIG. 5: Product ( $g^* m^*$ ) of the effective  $g$ -factor and effective mass in AlAs 2D electrons, deduced from data plotted in Figs. 2 and 3, normalized to its band value.  $g^* m^*$  is remarkably constant over most of the density range.

can assume single valley occupation. In Fig. 1, a less pronounced "kink" in  $R_{xx}$  can indeed be seen at  $B_{||} \approx 5$  T for the highest density, and may be related to the depopulation of one of the valleys.

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